OPA9451

Infrared LED Chip

GaAs/GaAs

1. Material

Substrate	GaAs	(N Type)
Epitaxial Layer	GaAs	(P/N Type)

2. Electrode

N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

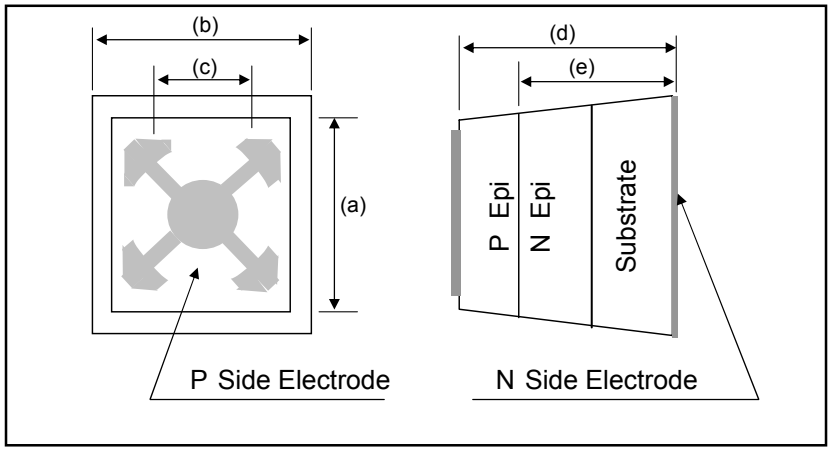
3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	V_F			1.6	V	IF=100mA
Reverse Voltage	V_R	8			V	IR=10uA
Power	P_O	0.479	0.62		mW	IF=50mA
Wavelength	λ_P		940		nm	IF=20mA
	$\Delta\lambda$		45		nm	IF=20mA

※ Note : Power is measured by Sorter E/T system with bare chip.

4. Mechanical Data

(a) Emission Area	----------	13.8mil x 13.8mil
(b) Bottom Area	----------	14.6mil x 14.6mil
(c) Bonding Pad	----------	135um
(d) Chip Thickness	----------	11mil
(e) Junction Height	----------	8.2mil



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